

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A photomask fabrication method, wherein mask correction units are established ~~based on space dependency of a pattern obtained by a photolithographic process and etching process,~~ and

~~design data for the~~ mask correction units for photomask fabrication is are corrected based on a comparison of the mask correction units with respect to actual measured variation of a manufactured structure from a desired structure.

2. (Currently Amended) A photomask fabrication method according to claim 1, wherein along with correcting said mask correction units ~~design data,~~ parameter settings for lithographic equipment are corrected according to ~~the~~ an XY differential ~~based on space dependency of said~~ of a resultant pattern.

3. (Currently Amended) A photomask fabricated by design data revised using mask correction units , ~~established based on space dependency of a pattern obtained by a photolithographic process and etching process.~~

wherein the mask correction units are determined by measuring variation of a manufactured structure from a desired structure.

4. (Currently Amended) A photomask according to claim 3, ~~wherein along with correction of said design data by~~ wherein said mask correction units, ~~said photomask is fabricated by mask lithographic equipment with parameter settings are corrected according in order to the~~ minimize an XY differential of said a resultant pattern based on the space dependency of said pattern.

5. (Canceled) Please cancel claim 5.

6. (Currently Amended) ~~An exposure method, wherein along with utilizing a~~
A photomask according to claim 3, wherein said ~~parameter settings~~ mask correction units ~~are corrected according to the~~ used to minimize an XY differential of said a resultant pattern based on space dependency of a pattern obtained by a photolithographic process and etching process, and a wafer is exposed to light with respect to a desired pattern.

Please add the following new claims:

7. (New) The photomask fabrication method according to claim 1, wherein actual length measurement results are used to revise the mask correction units.

8. (New) The photomask of claim 3, wherein actual length measurement results are used to revise the mask correction units.

9. (New) The photomask fabrication method according to claim 1, wherein a correction grid and correction table are utilized.

10. (New) The photomask of claim 3, wherein a correction grid and correction table are utilized.

11. (New) The photomask fabrication method according to claim 1, wherein if a measured average is not within less than twice absolute value of the correction grid value, the mask correction unit in the correction table is revised.

12. (New) The photomask of claim 3, wherein if a measured average is not within less than twice absolute value of the correction grid value, the mask correction unit in the correction table is revised.

13. (New) The photomask fabrication method according to claim 1, wherein an average of a line width in the X direction and a line width in the Y direction is determined, and if a differential between the measured value is greater than twice the absolute value of the mask correction unit, the mask correction unit in the correction table is revised.

14. (New) The photomask of claim 3, wherein an average of a line width in the X direction and a line width in the Y direction is determined, and if a differential between the measured value is greater than twice the absolute value of the mask correction unit, the mask correction unit in the correction table is revised.